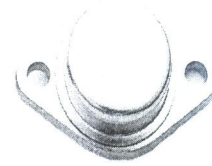


BD317MQ

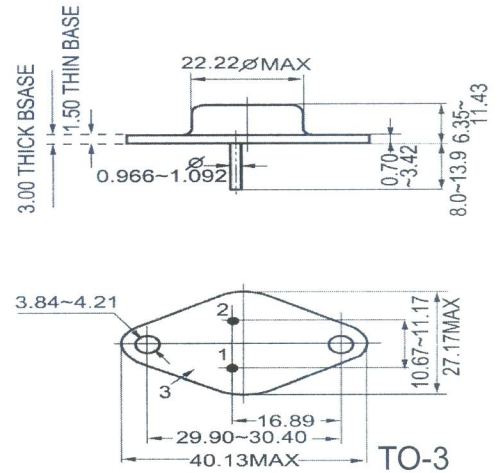
Silicon NPN Transistors

◆ **Features**

·With TO-3 package

◆ **Absolute Maximum Ratings Tc=25°C**

SYMBOL	PARAMETER	RATING	UNIT
V _{CBO}	Collector to base voltage	100	V
V _{CEO}	Collector to emitter voltage	100	V
V _{EBO}	Emitter to base voltage	5	V
I _{CP}	Peak collector current		A
I _C	Collector current	16	A
P _C	Collector power dissipation	100	W
T _j	Junction temperature	200	°C
T _{stg}	Storage temperature	-65~200	°C

◆ **Electrical Characteristics Tc=25°C**

SYMBOL	PARAMETER	CONDITIONS	MIN	Typ.	MAX	UNIT
I _{CBO}	Collector-base cut-off current					
I _{EBO}	Emitter-base cut-off current					
I _{CEO}	Collector-emitter cut-off current					
V _{CBO}	Collector-base breakdown voltage	I _C =1mA; I _E =0	100			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA; I _B =0	100			V
V _{EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			V
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =16A; I _B =4A			2.0	V
V _{CE(sat-2)}	Collector-emitter saturation voltages					
V _{CE(sat-3)}	Collector-emitter saturation voltages					
h _{FE-1}	Forward current transfer ratio	I _C =8A; V _{CE} =2V	20		80	
h _{FE-2}	Forward current transfer ratio					
V _{BE(sat)1}	Base-emitter saturation voltages					
V _{BE(sat)2}	Base-emitter saturation voltages					
V _{BE(sat)3}	Base-emitter saturation voltages					
f _T	Transition frequency					
V _{ob}	Collector Out put Capacitance					